

Siltronic ramps up GaN wafer activities with AIXTRON system

Order of fully automated AIX G5+ C system for positioning on the emerging market for GaN-on-Silicon materials applications / High throughput system with highest uniformity enables fast ramp-up

Herzogenrath/Germany, August 25, 2020 – Siltronic AG strengthens its GaN on Silicon wafer activities with an **AIX G5+ C** system of AIXTRON SE (FSE: AIXA), a worldwide leading provider of deposition equipment to the semiconductor industry. The AIX G5+ C system is fully automated and equipped with in-situ cleaning and a cassette-to-cassette transfer module for best epitaxial stability and unmatched low defect ratios. The State-of-the-art Planetary Reactor® includes AIXTRON's Auto-Feed Forward (AFF) individual on-wafer temperature control and has an 8x150-mm and 5x200-mm configuration. The system will be shipped to the customer in the fourth quarter of this year.

Wafer equipment for growing megatrends

Siltronic is a leading supplier of silicon wafers for the semiconductor industry and will use the additional epitaxy reactor to strengthen its position for the emerging GaN-on-Si market. The AIX G5+ C will be used by Siltronic for the production of 150 and 200 mm Gallium Nitride-on-Silicon (GaN-on-Si) epi wafer for Radio Frequency (RF) and power applications.

RF, power devices and circuit are enabling high switching frequencies and efficient energy management with high power densities. These features are required for rapidly growing applications such as data centers, renewable energy and the next generation of wireless networks (5G). Alongside the smaller form factor, GaN-on-Si is an ideal candidate for rapid charging and car electrification.

Chosen by the best in the industry

Dr. Christoph von Plotho, CEO of Siltronic AG, says: "The GaN-on-Si market is an important future growth field. We have been very active early on within the GaN Power Program of imec, the research institute for nanoelectronics, to provide our customers with leading edge performance. To position ourselves competitively in this market, we need a reactor which allows us to deliver our customers with the best performance epi-wafers while ramping up volume at lowest costs. We see the AIX G5+ C as the ideal solution in this regard both for GaN Power and RF devices to serve the growing applications and megatrends. The use of GaN-on-Si technology also makes a central contribution to improving the energy balance through decarbonization".

For further information please contact

Corporate Communications
AIXTRON SE, Dornkaulstr. 2, 52134 Herzogenrath, Germany
PHONE +49 (2407) 9030-444 FAX +49 (2407) 9030-445
E-MAIL info@aixtron.com WEB www.aixtron.com

“The GaN-on-Si technology has made impressive breakthrough in the last years and devices are rapidly gaining acceptance into both consumer and industrial products for power and RF application. The AIX G5+ C is a fully mature platform dedicated to these advanced applications, and it’s fantastic that we can accompany our customers to unlock these new markets”, says Dr. Felix Grawert, President of AIXTRON.

To download photos please click [here](#).

Contact person

Guido Pickert
Head of Investor Relations & Corporate Communications
PHONE +49 (2407) 9030-444
MOBILE +49 (173) 5407062
MAIL g.pickert@aixtron.com

About AIXTRON

AIXTRON SE is a leading provider of deposition equipment to the semiconductor industry. The Company was founded in 1983 and is headquartered in Herzogenrath (near Aachen), Germany, with subsidiaries and sales offices in Asia, United States and in Europe. AIXTRON’s technology solutions are used by a diverse range of customers worldwide to build advanced components for electronic and opto-electronic applications based on compound, silicon, or organic semiconductor materials. Such components are used in a broad range of innovative applications, technologies and industries. These include LED applications, display technologies, data storage, data transmission, energy management and conversion, communication, signaling and lighting as well as a range of other leading-edge technologies.

Our registered trademarks: AIXACT®, AIXTRON®, Atomic Level SolutionS®, Close Coupled Showerhead®, CRIUS®, Gas Foil Rotation®, OVPD®, Planetary Reactor®, PVPD®, TriJet®

For further information on AIXTRON (FSE: AIXA, ISIN DE000A0WMPJ6; OTC: AIXNY) please visit our website at: www.aixtron.com.

About Siltronic

Siltronic is one of the world's largest manufacturers of hyperpure silicon wafers and partner to many leading semiconductor companies. The company operates production sites in Asia, Europe and the USA. Siltronic develops and manufactures silicon wafers in diameters of up to 300 mm. Silicon wafers form the basis for modern microelectronics and nanoelectronics and are a key component in semiconductor chips driving computers, smartphones, navigation systems and many other applications. Siltronic AG employs around 3,600 people and is a stock-listed company in Germany (Prime Standard). Siltronic shares are included in the MDAX and TecDAX.

For further information on Siltronic AG please visit the company website at <https://www.siltronic.com/en/>.

For further information please contact

Corporate Communications
AIXTRON SE, Dornkaulstr. 2, 52134 Herzogenrath, Germany
PHONE +49 (2407) 9030-444 FAX +49 (2407) 9030-445
E-MAIL info@aixtron.com WEB www.aixtron.com

Forward-Looking Statements

This document may contain forward-looking statements regarding the business, results of operations, financial condition and earnings outlook of AIXTRON. These statements may be identified by words such as "may", "will", "expect", "anticipate", "contemplate", "intend", "plan", "believe", "continue" and "estimate" and variations of such words or similar expressions. These forward-looking statements are based on our current assessments, expectations and assumptions, of which many are beyond control of AIXTRON, and are subject to risks and uncertainties. You should not place undue reliance on these forward-looking statements. Should these risks or uncertainties materialize, or should underlying expectations not occur or assumptions prove incorrect, actual results, performance or achievements of AIXTRON may materially vary from those described explicitly or implicitly in the relevant forward-looking statement. This could result from a variety of factors, such as actual customer orders received by AIXTRON, the level of demand for deposition technology in the market, the timing of final acceptance of products by customers, the condition of financial markets and access to financing for AIXTRON, general conditions in the market for deposition plants and macroeconomic conditions, cancellations, rescheduling or delays in product shipments, production capacity constraints, extended sales and qualification cycles, difficulties in the production process, the general development in the semi-conductor industry, increased competition, fluctuations in exchange rates, availability of public funding, fluctuations and/or changes in interest rates, delays in developing and marketing new products, a deterioration of the general economic situation and any other factors discussed in any reports or other announcements, in particular in the chapter Risks in the Annual Report, filed by AIXTRON. Any forward-looking statements contained in this document are based on current expectations and projections of the executive board based on information available the date hereof. AIXTRON undertakes no obligation to revise or update any forward-looking statements as a result of new information, future events or otherwise, unless expressly required to do so by law.

This document is an English language translation of a document in German language. In case of discrepancies, the German language document shall prevail and shall be the valid version.

For further information please contact

Corporate Communications

AIXTRON SE, Dornkaulstr. 2, 52134 Herzogenrath, Germany

PHONE +49 (2407) 9030-444 **FAX** +49 (2407) 9030-445

E-MAIL info@aixtron.com **WEB** www.aixtron.com